

Method And Apparatus For Depositing An Epitaxial Layer On A Substrate Wafer Made Of Semiconductor Material

Abstract

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A method and an apparatus for depositing an epitaxial layer on a substrate wafer made of semiconductor material. The method comprises the arrangement of the substrate wafer and a susceptor in a deposition device such that the substrate wafer rests on the susceptor and the susceptor is held by arms of a support shaft;

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monitoring whether a misalignment of the susceptor exists with respect to its position relative to the position of a pre-heating ring surrounding it; monitoring whether a misalignment of the support shaft exists with respect to its position relative to the position of the pre-heating ring; if at least one of the misalignments is present, elimination of the respective misalignment; and the deposition of the epitaxial layer on

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the substrate wafer.

Drawing for the abstract: Fig. 1